

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicants	Wolfgang Dettman, <i>et al.</i>
Serial No. 10/	Filing Date: September 19, 2003
Title of Application:	Photomask, In Particular Alternating Phase Shift Mask, With Compensation Structure

Mail Stop Non-Fee Amendment  
 Commissioner for Patents  
 Post Office Box 1450  
 Alexandria, VA 22313-1450

**Preliminary Amendment**

Applicants herewith present its amendment and remarks. Please amend the claims and abstract as detailed below.

**In the Claims**

1. (currently amended) A mask (4), in particular photomask, for the production of semiconductor devices, comprising at least one product field area (6a) and a compensation structure (5) positioned outside the product field area (6a) characterized in that the compensation structure (5) comprises at least one electroconductive region (8b) which is electrically connected with the product field area (6a).
2. (currently amended) The mask (4), in particular photomask, for the production of semiconductor devices, in accordance with claim 1, wherein – viewed from the product field area (6a) – the electroconductive region (8b) extends path-shaped outwardly.
3. (currently amended) The mask (4), in particular photomask, for the production of semiconductor devices, in accordance with ~~claims 1 or~~ claim 2, wherein the path (8b) of the electroconductive region has a breadth (d) of between 1 nm and 30 nm or 200 nm and 5 mm, respectively, in particular between 1  $\mu$ m and 50  $\mu$ m, e.g. between 5  $\mu$ m and 25  $\mu$ m.